

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

BT151-MS

Product specification

FEATURES

- Glass-passivated mesa chip for reliability and uniform
- High current output up to 12A
- RoHS (2002/95/EC) compliant packages

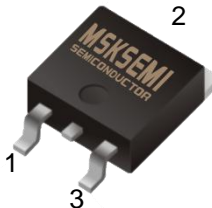
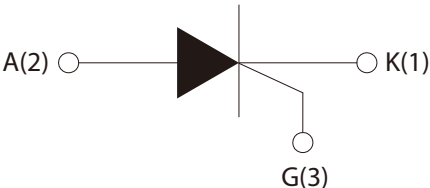

APPLICATIONS

- Motor cycle
- Power charger
- T-tools etc

APPROVALS

- RoHS: Compliance with 2011/65/EU
- HF: Compliance with IEC61249-2-21:2003

Reference News

TO-252	Schematic Symbol	MARKING
		

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage ($T_j=25^{\circ}\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}\text{C}$)	V_{RRM}	800	
RMS on-state current ($T_c=110^{\circ}\text{C}$)	$I_{\text{T(RMS)}}$	12	A
Non repetitive surge peak on-state current ($t_p=10\text{ms}$)	I_{TSM}	140	
I^2t value for fusing ($t_p=10\text{ms}$)	I^2t	98	A ² S
Critical rate of rise of on-state current ($I_G=2 \cdot I_{\text{GT}}$)	d_i/d_t	50	A/ μs
Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{\text{G(AV)}}$	1	W
Storage junction temperature range	T_{STG}	-40~+150	$^{\circ}\text{C}$
Operating junction temperature range	T_j	-40~+125	

ELECTRICAL CHARACTERISTICS (T_j=25°C)

Symbol	Test Condition	Value	Unit
I _{GT}	V _D =12V, R _L =33Ω	≤15	mA
V _{GT}		≤1.5	V
V _{GD}	V _D =V _{DRM} , R _L =3.3KΩ, T _j =150°C	≥0.2	
I _H	I _T =500mA	≤50	mA
I _L	I _G =1.2I _{GT}	≤60	
dV _D /dt	V _D =2/3, V _{DRM} Gate Open, T _j =150°C	≥200	V/μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value	Unit
V _{TM}	I _{TM} =24A, tp=380μs	T _j =25℃	≤1.55	V
I _{DRM}	V _D =V _{DRM} , V _R =V _{RRM}		≤5	uA
I _{RRM}		T _j =150℃	≤2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case(AC)	1.8	°C/W
R _{th(j-a)}	Junction to ambient	70	°C/W

PARAMETER CHARACTERISTIC CURVE

FIG.1 Maximum power dissipation versus RMS on-state current

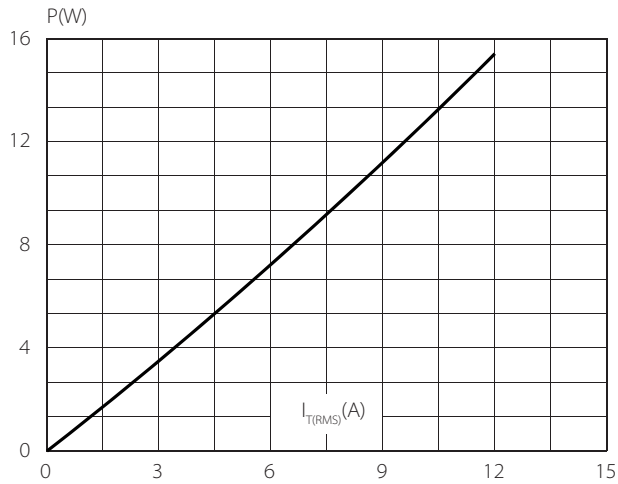


FIG.2: RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35μm)(full cycle)

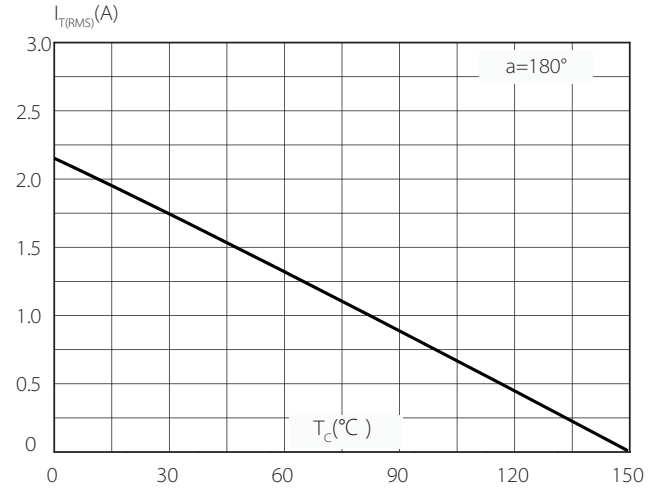


FIG.3: Surge peak on-state current versus number of cycles

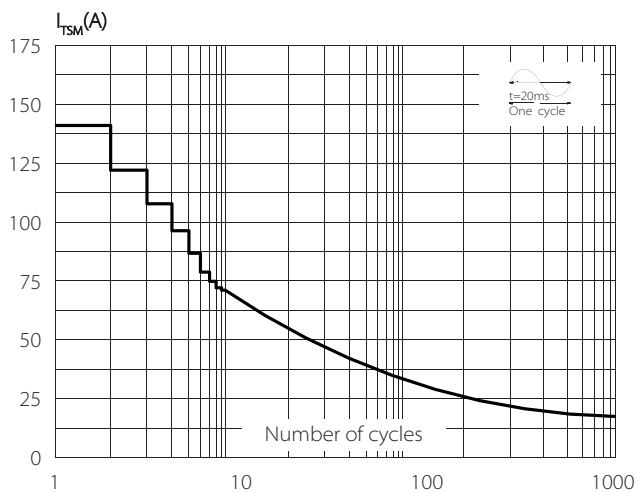


FIG.4 On-state characteristics (maximum values)

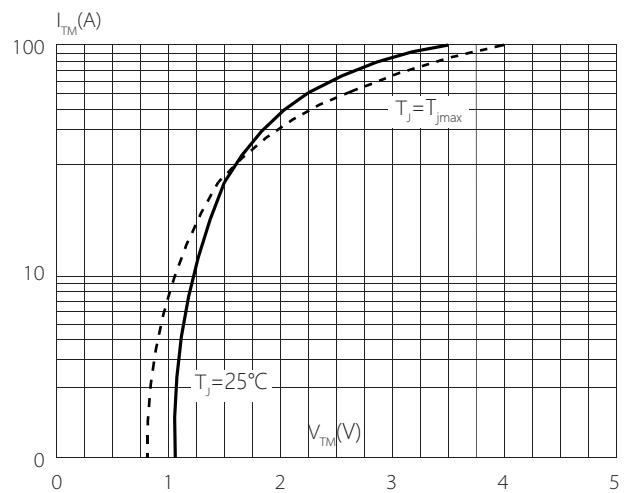


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$ and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

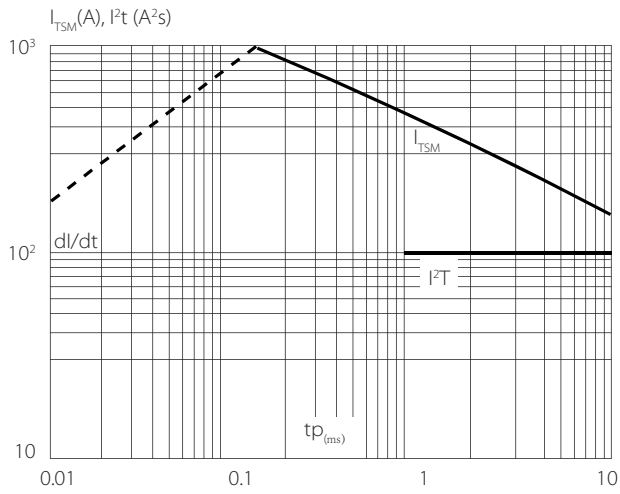


FIG.6 Relative variations of gate trigger current, holding current and latching current versus junction temperature

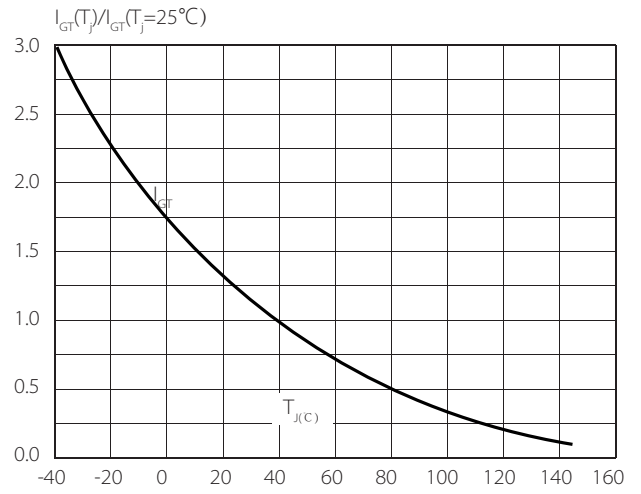


FIG.7 Relative variations of holding current versus junction temperature

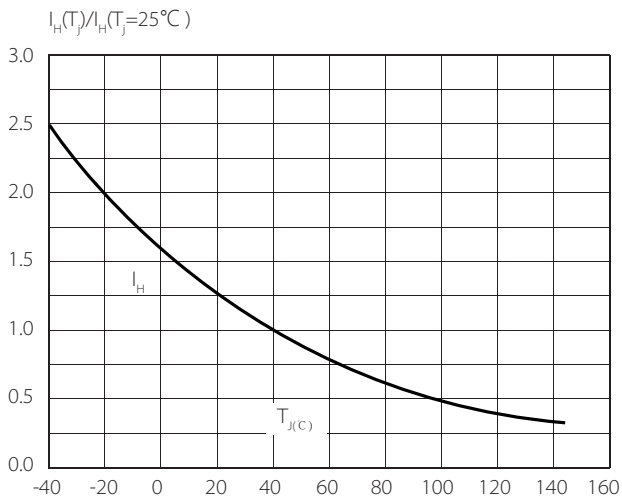
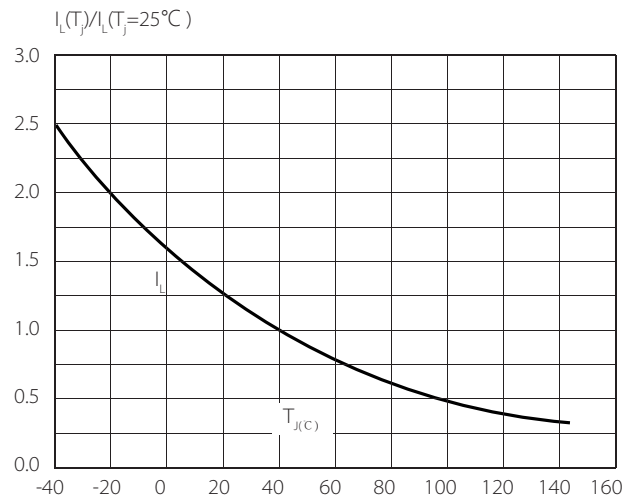
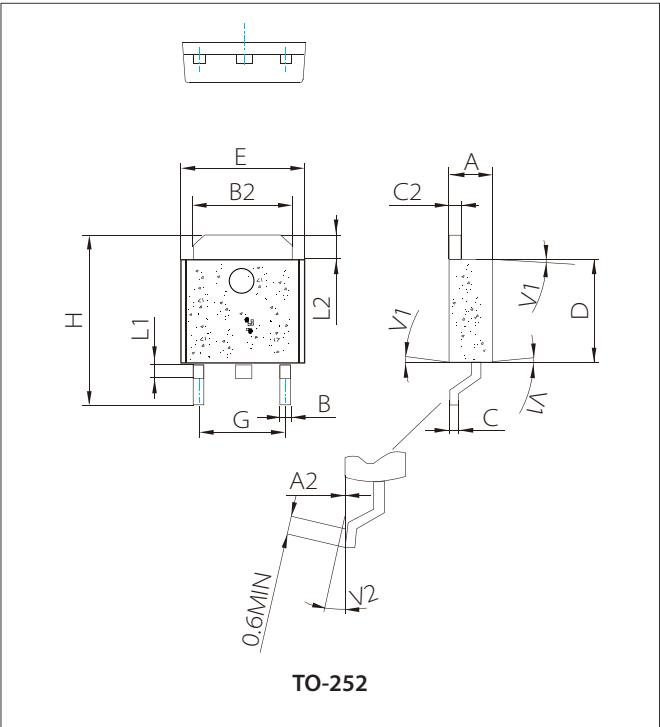


FIG.8 Relative variations of latching current versus junction temperature



PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173	0.1	0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051	0.143	0.067
L2	1.37		1.50	0.054		0.059
L1		4°			0.130	
V2	0°		8°	0°		8°

Order information

P/N	PKG	QTY
BT151-MS	TO-252	2500PCS

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